

AF/2826

GR 98 P 1379 D



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By:

Date: February 12, 2003 (3/5/03)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Lars-Peter Heineck et al.

Applic. No. : 09/885,553

Filed : June 20, 2001

Title : MOS Transistor in a Single-Transistor Memory Cell Having a Locally Thickened Gate Oxide

Examiner : Johannes P. Mondt

Group Art Unit : 2826

#9/B

Mondt
N/E

JMCmillan
2/06/03

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AMENDMENT under 37 C.F.R. § 1.116

BOX AF

Hon. Commissioner of Patents and Trademarks,
Washington, D. C. 20231

Sir:

Responsive to the final Office action dated November 13, 2002

kindly amend the above-identified application as follows:

In the Claims:

B1
Claim 1(Twice amended). A MOS transistor in a single-transistor memory cell, comprising: